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Incl	osure Material:
Meta	al
Ove	rall Length:
0.71	0 inches
Fun	ction For Which Designed:
Zen	er diode
Mou	Inting Facility Quantity:
1	
Μου	inting Method:
Thre	aded stud
Feat	ures Provided:
Herr	netically sealed case
Ove	rall Width Across Flats:
0.18	7 inches
Thre	ead Size:
0.11	2 inches
Sem	iconductor Material:
Silic	on
Volt	age Rating In Volts Per Characteristic:
6.8	regulator voltage
Volt	age Tolerance In Percent:
-5.0/	/+5.0
Cur	rent Rating Per Characteristic:
350.	00 milliamperes all primaries horsepower metric
Pow	er Rating Per Characteristic:
10.0	watts small-signal input power, common-collector preset
Мах	imum Operating Tempurature Per Measurement Point:
175.	0 degrees celsius ambient air
Pred	cious Material And Location:
	al surfaces gold
Pred	cious Material:
Golo	1
Thre	ead Series Designator:
Unc	
Terr	ninal Type And Quantity:
	lder stud and 1 threaded stud
She	If Life:
N/a	
Unit	Of Measure:
Den	nilitarization:
No	

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